

### Unbiased junction equations

$$V_{bi} = \frac{kT}{q} \ln \left( \frac{n(x_{n0})p(-x_{p0})}{n_i^2} \right)$$

$$= \frac{kT}{q} \ln \left( \frac{N_D N_A}{n_i^2} \right)$$

$$= kT \ln \left( \frac{p(-x_{p0})}{p(x_{n0})} \right)$$

$$= kT \ln \left( \frac{n(x_{n0})}{n(-x_{p0})} \right)$$

$$= \frac{qN_D}{2\epsilon} (x_{n0})^2 + \frac{qN_A}{2\epsilon} (x_{p0})^2$$

$$= \frac{1}{2} \frac{q}{\epsilon} \frac{N_A N_D}{(N_A + N_D)} w^2$$

$$x_{n0} = \left( \frac{2\epsilon N_A V_{bi}}{qN_D (N_A + N_D)} \right)^{1/2}$$

$$= w \frac{N_A}{(N_A + N_D)}$$

$$x_{p0} = \frac{x_{n0} N_D}{N_A} = \left( \frac{2\epsilon V_{bi} N_D}{qN_A (N_A + N_D)} \right)^{1/2}$$

$$= w \frac{N_D}{(N_A + N_D)}$$

$$w = x_{n0} + x_{p0}$$

$$= \left( \frac{2\epsilon V_{bi} (N_A + N_D)}{qN_A N_D} \right)^{1/2}$$

$$E_{xp} = \int_{-x_{p0}}^x -\frac{qN_A}{\epsilon} dx$$

$$= -\frac{qN_A}{\epsilon} (x + x_{p0})$$

$$E_{xn} = \int_x^{x_{n0}} \frac{qN_D}{\epsilon} dx$$

$$= \frac{qN_D}{\epsilon} (x_{n0} - x)$$

$$Q_p = Aq x_{n0} N_D$$

$$Q_n = -Aq x_{p0} N_A$$

$$Q_p + Q_n = 0$$

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$$x_{n0} N_D = x_{p0} N_A$$

### Time independent Biased junctions

$$\Delta n_p = \frac{n_i^2}{N_A} \left( e^{qV_A/kT} - 1 \right) e^{+(x+x_{p0})/L_n}$$

$$\Delta p_n = \frac{n_i^2}{N_D} \left( e^{qV_A/kT} - 1 \right) e^{-(x-x_{n0})/L_p}$$

Minority currents density

$$J_N = qD_n \frac{\partial \Delta n_p(x)}{\partial x}$$

$$= \frac{qD_n}{L_n} \Delta n_p(x)$$

$$J_P = -qD_p \frac{\partial \Delta p_n(x)}{\partial x}$$

$$= \frac{qD_p}{L_p} \Delta p_n(x)$$

Total current is

$$I = I_0 \left( e^{qV_A/kT} - 1 \right)$$

$$I_0 = qn_i^2 A \left( \frac{D_n}{L_n N_A} + \frac{D_p}{L_p N_D} \right)$$

$$I_{P_{total}} = \frac{Q_p}{\tau_p}$$

$$I_{N_{total}} = \frac{Q_n}{\tau_n}$$

$$w = x_{n0} + x_{p0}$$

$$= \left( \frac{2\epsilon(V_{bi} - V_A)(N_A + N_D)}{qN_A N_D} \right)^{1/2}$$

Total injected charge

$$Q_p = qAL_p p_{n0} \left( e^{qV_A/kT} - 1 \right)$$

$$Q_n = qAL_n n_{p0} \left( e^{qV_A/kT} - 1 \right)$$

### Time varying junctions

$i_D$  = Total current through the diode

$I_D$  = DC current through the diode

$i_d$  = AC current through the diode

$$i_D(t) = I_D + i_d(t)$$

$v_A$  = Total voltage across the diode

$V_A$  = DC voltage across the diode

$v_a$  = AC voltage across the diode

$$v_A(t) = V_A + v_a(t)$$

$$i_D(t) = \frac{Q(t)}{\tau} + \frac{dQ(t)}{dt}$$

$$v_A = \frac{kT}{q} \ln \left( \frac{I_F \tau_p}{qAL_p p_{n0}} \exp[-t/\tau_p] + 1 \right)$$

Storage delay time

$$t_{sd} = \tau_p \ln \left[ \frac{I_f + I_r}{I_r} \right] \quad t_{sd} = \tau_p \left( \operatorname{erf}^{-1} \left[ \frac{I_r}{I_f + I_r} \right] \right)^2$$

### Turn on transient

$$v_A = \frac{kT}{q} \ln \left[ \frac{I_F}{I_0} \left( 1 - e^{-t/\tau_p} \right) + 1 \right]$$

### Diode capacitance/resistance

#### Reverse Bias Capacitance

$$C = \epsilon A \left( \frac{qN_A N_D}{2\epsilon(N_A + N_D)(V_{bi} - v_A)} \right)^{1/2}$$

$$= \frac{\epsilon A}{w}$$

$$\equiv C_j$$

$$G_0 = \frac{q}{kT} (I + I_0)$$

$\approx 0$  in reverse bias

#### Forward Bias (again low frequency)

$$Q_p = qAL_p p_{n0} \left( e^{qV_A/kT} - 1 \right)$$

$$\approx qAL_p p_{n0} e^{qV_A/kT}$$

$$C = \frac{q}{kT} I \tau_p \left[ = \frac{q}{kT} (I - I_0) \tau_p \text{ - if done without approximations} \right]$$

$$\equiv C_S$$

$$C_S \approx G_0 \tau_p$$

### Metal-Semiconductor Junctions

$$V_{bi} = \phi_M - \phi_S$$

$$\phi_B = (\phi_M - \chi)$$

$$I_{total} = I_0 \left( e^{qV_A/kT} - 1 \right)$$

### Useful equations

deBroglie momentum

$$p = h / \lambda = \hbar k$$

Heisenberg uncertainty principle

$$\Delta p \Delta x \geq \hbar$$

$$\Delta E \Delta t \geq \hbar$$

Photon energy

$$E_{\text{photon}} = h\nu$$

$$r_n = \frac{\hbar^2 n^2}{m e^2}$$

Bohr Model

$$= 0.529 \text{ \AA} n^2$$

$$E_{\text{Bohr}} = -\frac{1}{2} \frac{m e^4}{\hbar^2 n^2}$$

$$= -13.56 \text{ eV} / n^2$$

Schrödinger's equation

$$\left( -\frac{\hbar^2}{2m} \nabla^2 + V \right) \Psi(\mathbf{r}, t) = -\frac{\hbar}{j} \partial_t \Psi(\mathbf{r}, t)$$

Maxwellian distribution

$$f(v) = n \left( \frac{m}{2\pi kT} \right)^{3/2} \exp \left[ \frac{-m(v)^2}{2kT} \right]$$

$$f(\mathcal{E}) = n \frac{1}{kT} \exp \left[ \frac{-\mathcal{E}}{kT} \right]$$

Equation of motion

$$\mathbf{F}_n = -e\mathbf{E} = m_n^* \mathbf{a} \quad (\text{electron})$$

$$\mathbf{F}_p = +e\mathbf{E} = m_p^* \mathbf{a} \quad (\text{hole})$$

Fermi-Dirac function.

$$f(\mathcal{E}) = \frac{1}{1 + \exp\left[\frac{(\mathcal{E} - \mathcal{E}_F)}{kT}\right]}$$

$$N_c(\mathcal{E})d\mathcal{E} = \frac{\sqrt{2}}{\pi^2} \left(\frac{m^*}{\hbar^2}\right)^{3/2} \sqrt{\mathcal{E} - \mathcal{E}_c} d\mathcal{E} \quad \text{Conduction band}$$

$$N_v(\mathcal{E})d\mathcal{E} = \frac{\sqrt{2}}{\pi^2} \left(\frac{m^*}{\hbar^2}\right)^{3/2} \sqrt{\mathcal{E}_v - \mathcal{E}} d\mathcal{E} \quad \text{Valance band}$$

STATE DENSITY

state distribution function.

$$n(\mathcal{E})d\mathcal{E} = f(\mathcal{E})N_c(\mathcal{E})d\mathcal{E} = \frac{1}{1 + \exp\left[\frac{(\mathcal{E} - \mathcal{E}_F)}{kT}\right]} \frac{\sqrt{2}}{\pi^2} \left(\frac{m^*}{\hbar^2}\right)^{3/2} \sqrt{\mathcal{E} - \mathcal{E}_c} d\mathcal{E} \quad \text{Electrons in the Conduction band}$$

$$p(\mathcal{E})d\mathcal{E} = (1 - f(\mathcal{E}))N_v(\mathcal{E})d\mathcal{E} = \left(1 - \frac{1}{1 + \exp\left[\frac{(\mathcal{E} - \mathcal{E}_F)}{kT}\right]}\right) \frac{\sqrt{2}}{\pi^2} \left(\frac{m^*}{\hbar^2}\right)^{3/2} \sqrt{\mathcal{E}_v - \mathcal{E}} d\mathcal{E} \quad \text{Holes in the Valance band}$$

$$n_0 \approx N_c \exp\left[\frac{-(\mathcal{E}_c - \mathcal{E}_F)}{kT}\right] = n_i \exp\left[\frac{(\mathcal{E}_F - \mathcal{E}_i)}{kT}\right]$$

$$p_0 \approx N_v \exp\left[\frac{(\mathcal{E}_v - \mathcal{E}_F)}{kT}\right] = n_i \exp\left[\frac{-(\mathcal{E}_F - \mathcal{E}_i)}{kT}\right]$$

total number of electrons and holes

$$n_i^2 = np$$

$$N_c = 2 \left(\frac{m_n^* kT}{2\pi\hbar^2}\right)^{3/2}$$

$$N_v = 2 \left(\frac{m_p^* kT}{2\pi\hbar^2}\right)^{3/2}$$

$$\mathcal{E}_i = \frac{(\mathcal{E}_v + \mathcal{E}_c)}{2} + \frac{kT}{2} \ln\left(\left(\frac{m_p^*}{m_n^*}\right)^{3/2}\right)$$

Intrinsic Energy

$$\mu_n = -\frac{\langle v \rangle}{E} = \frac{\tau |q|}{m_n^*}$$

$$\mu_p = \frac{\langle v \rangle}{E} = \frac{\tau |q|}{m_p^*}$$

Mobility

$$\begin{aligned} \mathbf{J} &= nq\langle \mathbf{v} \rangle \\ &= q(n_0\mu_n + p_0\mu_p)\mathbf{E} \\ &= \sigma\mathbf{E} \\ &= \mathbf{E} / \rho \end{aligned}$$

Conduction

$$D_n = \mu_n \frac{kT}{q_n}$$

Diffusion

$$D_p = \mu_p \frac{kT}{q_p}$$

Diffusion length

$$L_n = \sqrt{D_n \tau_n}$$

Diffusion time

$$\tau = \frac{1}{\alpha_r(p_0 + n_0)}$$